

Welcome to [E-XFL.COM](https://www.e-xfl.com)

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	75264
Total RAM Bits	516096
Number of I/O	341
Number of Gates	3000000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	484-BGA
Supplier Device Package	484-FPBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agle3000v2-fg484

Specify I/O States During Programming

Load from file... Save to file... ☐ Show BSR Details

	Port Name	Macro Cell	Pin Number	I/O State (Output Only)
	BIST	ADLIB:INBUF	T2	1
	BYPASS_IO	ADLIB:INBUF	K1	1
	CLK	ADLIB:INBUF	B1	1
	ENDOUT	ADLIB:INBUF	J16	1
	LED	ADLIB:OUTBUF	M3	0
	MONITOR[0]	ADLIB:OUTBUF	B5	0
	MONITOR[1]	ADLIB:OUTBUF	C7	Z
	MONITOR[2]	ADLIB:OUTBUF	D9	Z
	MONITOR[3]	ADLIB:OUTBUF	D7	Z
	MONITOR[4]	ADLIB:OUTBUF	A11	Z
	OEa	ADLIB:INBUF	E4	Z
	OEb	ADLIB:INBUF	F1	Z
	OSC_EN	ADLIB:INBUF	K3	Z
	PAD[10]	ADLIB:BIBUF_LVCMOS33U	M8	Z
	PAD[11]	ADLIB:BIBUF_LVCMOS33D	R7	Z
	PAD[12]	ADLIB:BIBUF_LVCMOS33U	D11	Z
	PAD[13]	ADLIB:BIBUF_LVCMOS33D	C12	Z
	PAD[14]	ADLIB:BIBUF_LVCMOS33U	R6	Z

Help OK Cancel

Figure 1-4 • I/O States During Programming Window

- Click OK to return to the FlashPoint – Programming File Generator window.

Note: I/O States During programming are saved to the ADB and resulting programming files after completing programming file generation.

2 – IGLOOe DC and Switching Characteristics

General Specifications

Operating Conditions

Stresses beyond those listed in [Table 2-1](#) may cause permanent damage to the device.

Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Absolute Maximum Ratings are stress ratings only; functional operation of the device at these or any other conditions beyond those listed under the Recommended Operating Conditions specified in [Table 2-2 on page 2-2](#) is not implied.

Table 2-1 • Absolute Maximum Ratings

Symbol	Parameter	Limits	Units
VCC	DC core supply voltage	–0.3 to 1.65	V
VJTAG	JTAG DC voltage	–0.3 to 3.75	V
VPUMP	Programming voltage	–0.3 to 3.75	V
VCCPLL	Analog power supply (PLL)	–0.3 to 1.65	V
VCCI and VMV ³	DC I/O buffer supply voltage	–0.3 to 3.75	V
VI	I/O input voltage	–0.3 V to 3.6 V (when I/O hot insertion mode is enabled) –0.3 V to (VCCI + 1 V) or 3.6 V, whichever voltage is lower (when I/O hot-insertion mode is disabled)	V
T _{STG} ²	Storage temperature	–65 to +150	°C
T _J ²	Junction temperature	+125	°C

Notes:

1. The device should be operated within the limits specified by the datasheet. During transitions, the input signal may undershoot or overshoot according to the limits shown in [Table 2-4 on page 2-3](#).
2. For flash programming and retention maximum limits, refer to [Table 2-3 on page 2-3](#), and for recommended operating limits, refer to [Table 2-2 on page 2-2](#).
3. VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on [page 3-1](#) for further information.

Table 2-2 • Recommended Operating Conditions ¹

Symbol	Parameter		Commercial	Industrial	Units
T _A	Ambient Temperature		0 to +70	–40 to +85	°C
T _J	Junction Temperature ²		0 to + 85	–40 to +100	°C
VCC ³	1.5 V DC core supply voltage ⁴		1.425 to 1.575	1.425 to 1.575	V
	1.2 V–1.5 V wide range DC core voltage ^{5, 6}		1.14 to 1.575	1.14 to 1.575	V
VJTAG	JTAG DC voltage		1.4 to 3.6	1.4 to 3.6	V
VPUMP	Programming voltage ⁶	Programming Mode	3.15 to 3.45	3.15 to 3.45	V
		Operation ⁷	0 to 3.6	0 to 3.6	V
VCCPLL ⁸	Analog power supply (PLL)	1.5 V DC core supply voltage ⁴	1.425 to 1.575	1.425 to 1.575	V
		1.2 V–1.5 V DC core supply voltage ⁵	1.14 to 1.575	1.14 to 1.575	V
VCCI and VMV ⁹	1.2 V DC supply voltage ⁵		1.14 to 1.26	1.14 to 1.26	V
	1.2 V wide range DC supply voltage ⁵		1.14 to 1.575	1.14 to 1.575	V
	1.5 V DC supply voltage		1.425 to 1.575	1.425 to 1.575	V
	1.8 V DC supply voltage		1.7 to 1.9	1.7 to 1.9	V
	2.5 V DC supply voltage		2.3 to 2.7	2.3 to 2.7	V
	3.0 V DC supply voltage ¹⁰		2.7 to 3.6	2.7 to 3.6	V
	3.3 V DC supply voltage		3.0 to 3.6	3.0 to 3.6	V
	LVDS differential I/O		2.375 to 2.625	2.375 to 2.625	V
	LVPECL differential I/O		3.0 to 3.6	3.0 to 3.6	V

Notes:

1. All parameters representing voltages are measured with respect to GND unless otherwise specified.
2. To ensure targeted reliability standards are met across ambient and junction operating temperatures, Microsemi recommends that the user follow best design practices using Microsemi's timing and power simulation tools.
3. The ranges given here are for power supplies only. The recommended input voltage ranges specific to each I/O standard are given in [Table 2-21 on page 2-20](#). VCCI should be at the same voltage within a given I/O bank.
4. For IGLOOe V5 devices
5. For IGLOOe V2 devices only, operating at VCCI ≥ VCC
6. All IGLOOe devices (V5 and V2) must be programmed with the VCC core voltage at 1.5 V. Applications using the V2 devices powered by a 1.2 V supply must switch the core supply to 1.5 V for in-system programming.
7. VPUMP can be left floating during operation (not programming mode).
8. VCCPLL pins should be tied to VCC pins. See the "[VCCPLA/B/C/D/E/F PLL Supply Voltage](#)" section for further information.
9. VMV pins must be connected to the corresponding VCCI pins. See the "[VMVx I/O Supply Voltage \(quiet\)](#)" section for further information.
10. 3.3 V wide range is compliant to the JESD8-B specification and supports 3.0 V VCCI operation.

- JTAG supply, PLL power supplies, and charge pump VPUMP supply have no influence on I/O behavior.

PLL Behavior at Brownout Condition

Microsemi recommends using monotonic power supplies or voltage regulators to ensure proper powerup behavior. Power ramp-up should be monotonic at least until VCC and VCCPLX exceed brownout activation levels. The VCC activation level is specified as 1.1 V worst-case (see Figure 2-1 and Figure 2-2 on page 2-5 for more details).

When PLL power supply voltage and/or VCC levels drop below the VCC brownout levels ($0.75\text{ V} \pm 0.25\text{ V}$), the PLL output lock signal goes low and/or the output clock is lost. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" chapter of the *IGLOOe FPGA Fabric User's Guide* for information on clock and lock recovery.

Internal Power-Up Activation Sequence

1. Core
2. Input buffers

Output buffers, after 200 ns delay from input buffer activation.

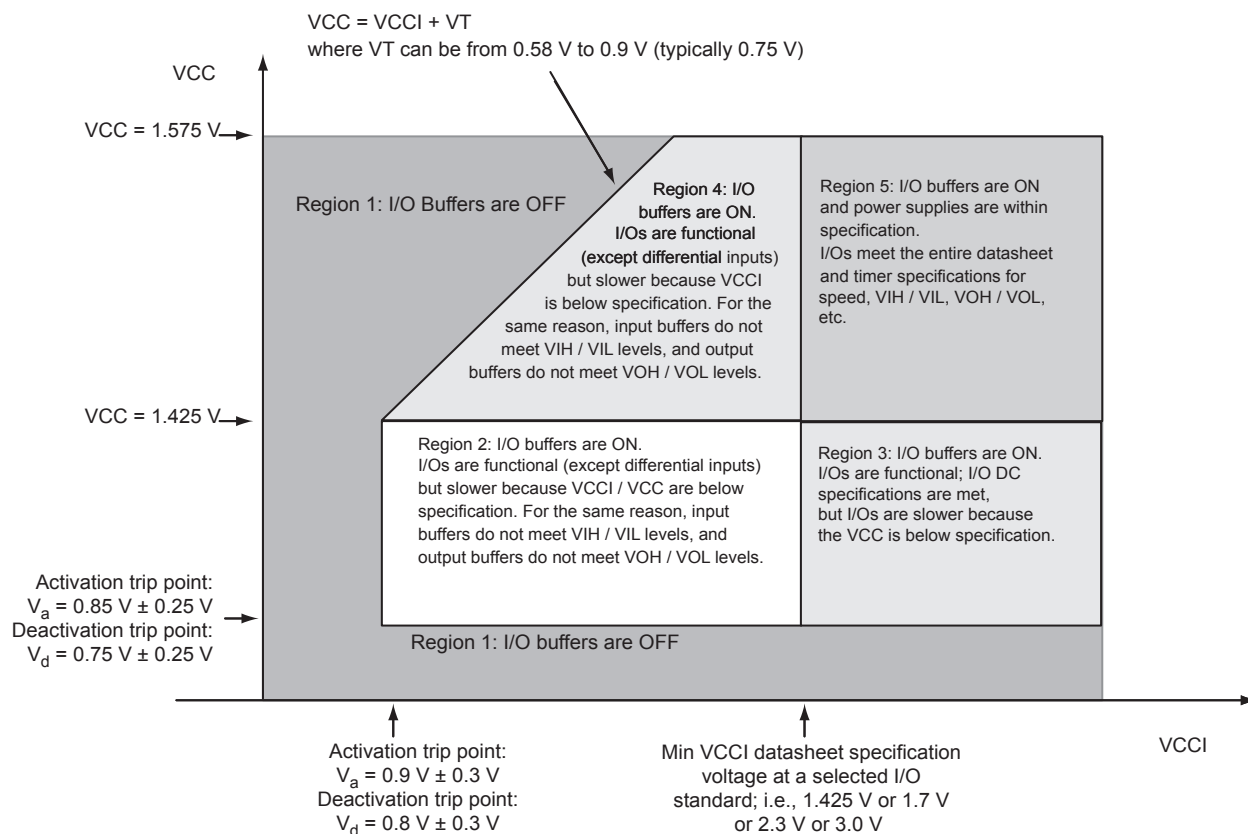


Figure 2-1 • V5 – I/O State as a Function of VCCI and VCC Voltage Levels

Package Thermal Characteristics

The device junction-to-case thermal resistivity is θ_{jc} and the junction-to-ambient air thermal resistivity is θ_{ja} . The thermal characteristics for θ_{ja} are shown for two air flow rates. The absolute maximum junction temperature is 100°C. EQ 2 shows a sample calculation of the absolute maximum power dissipation allowed for an 896-pin FBGA package at commercial temperature and in still air.

$$\text{Maximum Power Allowed} = \frac{\text{Max. junction temp. (}^{\circ}\text{C)} - \text{Max. ambient temp. (}^{\circ}\text{C)}}{\theta_{ja} (^{\circ}\text{C/W)}} = \frac{100^{\circ}\text{C} - 70^{\circ}\text{C}}{13.6^{\circ}\text{C/W}} = 2.206 \text{ W}$$

EQ 2

Table 2-5 • Package Thermal Resistivities

Package Type	Pin Count	θ_{jc}	θ_{ja}			Units
			Still Air	200 ft./min.	500 ft./min.	
Plastic Quad Flat Package (PQFP)	208	8.0	26.1	22.5	20.8	C/W
Plastic Quad Flat Package (PQFP) with embedded heat spreader	208	3.8	16.2	13.3	11.9	C/W
Fine Pitch Ball Grid Array (FBGA)	256	3.8	26.9	22.8	21.5	C/W
	484	3.2	20.5	17.0	15.9	C/W
	676	3.2	16.4	13.0	12.0	C/W
	896	2.4	13.6	10.4	9.4	C/W

Temperature and Voltage Derating Factors

Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays
(normalized to $T_J = 70^{\circ}\text{C}$, $V_{CC} = 1.425 \text{ V}$)
For IGLOOe V2 or V5 devices, 1.5 V DC Core Supply Voltage

Array Voltage VCC (V)	Junction Temperature ($^{\circ}\text{C}$)					
	-40°C	0°C	25°C	70°C	85°C	100°C
1.425	0.945	0.965	0.978	1.000	1.008	1.013
1.500	0.876	0.893	0.906	0.927	0.934	0.940
1.575	0.824	0.840	0.852	0.872	0.879	0.884

Table 2-7 • Temperature and Voltage Derating Factors for Timing Delays
(normalized to $T_J = 70^{\circ}\text{C}$, $V_{CC} = 1.14 \text{ V}$)
For IGLOOe V2, 1.2 V DC Core Supply Voltage

Array Voltage VCC (V)	Junction Temperature ($^{\circ}\text{C}$)					
	-40°C	0°C	25°C	70°C	85°C	100°C
1.14	0.968	0.978	0.991	1.000	1.006	1.010
1.20	0.864	0.873	0.885	0.893	0.898	0.902
1.26	0.793	0.803	0.813	0.821	0.826	0.829

Table 2-17 • Different Components Contributing to the Dynamic Power Consumption in IGLOOe Devices For IGLOOe V2 Devices, 1.2 V DC Core Supply Voltage

Parameter	Definition	Device-Specific Dynamic Contributions ($\mu\text{W}/\text{MHz}$)	
		AGLE600	AGLE3000
PAC1	Clock contribution of a Global Rib	12.61	8.17
PAC2	Clock contribution of a Global Spine	2.66	1.18
PAC3	Clock contribution of a VersaTile row	0.56	
PAC4	Clock contribution of a VersaTile used as a sequential module	0.071	
PAC5	First contribution of a VersaTile used as a sequential module	0.045	
PAC6	Second contribution of a VersaTile used as a sequential module	0.186	
PAC7	Contribution of a VersaTile used as a combinatorial module	0.109	
PAC8	Average contribution of a routing net	0.449	
PAC9	Contribution of an I/O input pin (standard-dependent)	See Table 2-9 on page 2-7.	
PAC10	Contribution of an I/O output pin (standard-dependent)	See Table 2-10 on page 2-7 and Table 2-11 on page 2-7.	
PAC11	Average contribution of a RAM block during a read operation	25.00	
PAC12	Average contribution of a RAM block during a write operation	30.00	
PAC13	Dynamic PLL contribution	2.10	

Note: For a different output load, drive strength, or slew rate, Microsemi recommends using the Microsemi power calculator or SmartPower in Libero SoC software.

Table 2-18 • Different Components Contributing to the Static Power Consumption in IGLOO Devices For IGLOOe V2 Devices, 1.2 V DC Core Supply Voltage

Parameter	Definition	Device Specific Static Power (mW)	
		AGLE600	AGLE3000
PDC1	Array static power in Active mode	See Table 2-12 on page 2-8.	
PDC2	Array static power in Static (Idle) mode	See Table 2-11 on page 2-7.	
PDC3	Array static power in Flash*Freeze mode	See Table 2-9 on page 2-7.	
PDC4	Static PLL contribution	0.90	
PDC5	Bank quiescent power (VCCI-dependent)	See Table 2-12 on page 2-8.	
PDC6	I/O input pin static power (standard-dependent)	See Table 2-13 on page 2-9.	
PDC7	I/O output pin static power (standard-dependent)	See Table 2-14 on page 2-10.	

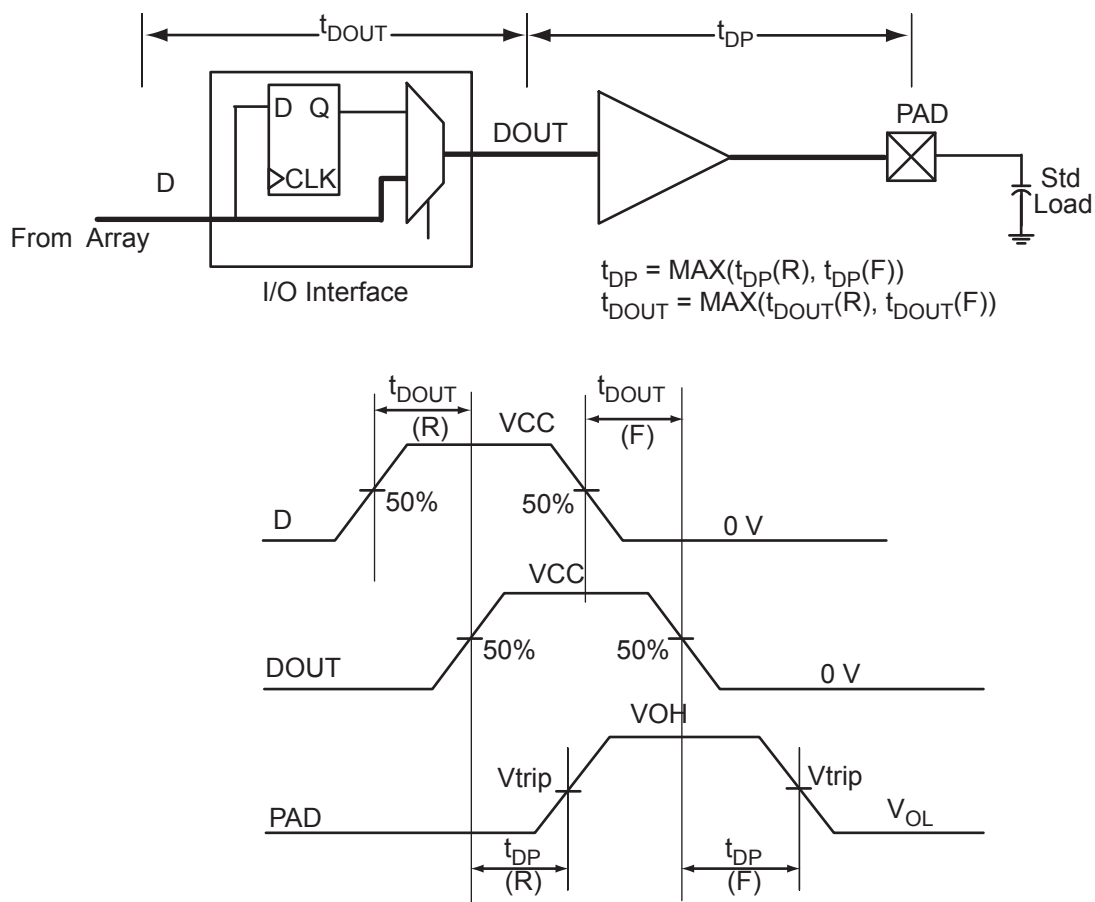


Figure 2-5 • Output Buffer Model and Delays (example)

Timing Characteristics

1.5 V DC Core Voltage

Table 2-54 • 1.8 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	7.33	0.18	1.27	1.59	0.66	7.47	6.18	2.34	1.18	11.07	9.77	ns
4 mA	Std.	0.97	6.07	0.18	1.27	1.59	0.66	6.20	5.25	2.69	2.42	9.79	8.84	ns
6 mA	Std.	0.97	5.18	0.18	1.27	1.59	0.66	5.29	4.61	2.93	2.88	8.88	8.21	ns
8 mA	Std.	0.97	4.88	0.18	1.27	1.59	0.66	4.98	4.48	2.99	3.01	8.58	8.08	ns
12 mA	Std.	0.97	4.80	0.18	1.27	1.59	0.66	4.89	4.49	3.07	3.47	8.49	8.09	ns
16 mA	Std.	0.97	4.80	0.18	1.27	1.59	0.66	4.89	4.49	3.07	3.47	8.49	8.09	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-55 • 1.8 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	3.43	0.18	1.27	1.59	0.66	3.51	3.39	2.33	1.19	7.10	6.98	ns
4 mA	Std.	0.97	2.83	0.18	1.27	1.59	0.66	2.89	2.59	2.69	2.49	6.48	6.18	ns
6 mA	Std.	0.97	2.45	0.18	1.27	1.59	0.66	2.51	2.19	2.93	2.95	6.10	5.79	ns
8 mA	Std.	0.97	2.38	0.18	1.27	1.59	0.66	2.43	2.12	2.98	3.08	6.03	5.71	ns
12 mA	Std.	0.97	2.37	0.18	1.27	1.59	0.66	2.42	2.03	3.07	3.57	6.02	5.62	ns
16 mA	Std.	0.97	2.37	0.18	1.27	1.59	0.66	2.42	2.03	3.07	3.57	6.02	5.62	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Timing Characteristics

1.5 V DC Core Voltage

Table 2-60 • 1.5 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	7.61	0.18	1.47	1.77	0.66	7.76	6.33	2.81	2.34	11.36	9.92	ns
4 mA	Std.	0.97	6.54	0.18	1.47	1.77	0.66	6.67	5.56	3.09	2.88	10.26	9.16	ns
6 mA	Std.	0.97	6.15	0.18	1.47	1.77	0.66	6.27	5.42	3.15	3.02	9.87	9.02	ns
8 mA	Std.	0.97	6.07	0.18	1.47	1.77	0.66	6.20	5.42	2.64	3.56	9.79	9.02	ns
12 mA	Std.	0.97	6.07	0.18	1.47	1.77	0.66	6.20	5.42	2.64	3.56	9.79	9.02	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-61 • 1.5 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	3.25	0.18	1.47	1.77	0.66	3.32	3.00	2.80	2.43	6.92	6.59	ns
4 mA	Std.	0.97	2.81	0.18	1.47	1.77	0.66	2.87	2.51	3.08	2.97	6.46	6.10	ns
6 mA	Std.	0.97	2.72	0.18	1.47	1.77	0.66	2.78	2.41	3.14	3.12	6.37	6.01	ns
8 mA	Std.	0.97	2.69	0.18	1.47	1.77	0.66	2.75	2.30	3.24	3.67	6.35	5.89	ns
12 mA	Std.	0.97	2.69	0.18	1.47	1.77	0.66	2.75	2.30	3.24	3.67	6.35	5.89	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

1.2 V DC Core Voltage

Table 2-62 • 1.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	8.53	0.26	1.72	2.16	1.10	8.67	7.05	3.39	3.09	14.46	12.83	ns
4 mA	Std.	1.55	7.34	0.26	1.72	2.16	1.10	7.46	6.22	3.70	3.73	13.25	12.01	ns
6 mA	Std.	1.55	6.91	0.26	1.72	2.16	1.10	7.03	6.07	3.77	3.90	12.82	11.85	ns
8 mA	Std.	1.55	6.83	0.26	1.72	2.16	1.10	6.94	6.07	2.91	4.54	12.73	11.86	ns
12 mA	Std.	1.55	6.83	0.26	1.72	2.16	1.10	6.94	6.07	2.91	4.54	12.73	11.86	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-6](#) for derating values.

Table 2-63 • 1.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.72	0.26	1.72	2.16	1.10	3.78	3.45	3.38	3.19	9.56	9.24	ns
4 mA	Std.	1.55	3.23	0.26	1.72	2.16	1.10	3.27	2.92	3.69	3.83	9.06	8.71	ns
6 mA	Std.	1.55	3.13	0.26	1.72	2.16	1.10	3.18	2.82	3.76	4.01	8.96	8.61	ns
8 mA	Std.	1.55	3.10	0.26	1.72	2.16	1.10	3.15	2.70	3.86	4.68	8.93	8.49	ns
12 mA	Std.	1.55	3.10	0.26	1.72	2.16	1.10	3.15	2.70	3.86	4.68	8.93	8.49	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-7 on page 2-6](#) for derating values.

HSTL Class II

High-Speed Transceiver Logic is a general-purpose high-speed 1.5 V bus standard (EIA/JESD8-6). IGLOOe devices support Class II. This provides a differential amplifier input buffer and a push-pull output buffer.

Table 2-93 • Minimum and Maximum DC Input and Output Levels

HSTL Class II	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
15 mA ⁵	-0.3	VREF - 0.1	VREF + 0.1	3.6	0.4	VCCI - 0.4	15	15	66	55	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operating conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Output drive strength is below JEDEC specification.

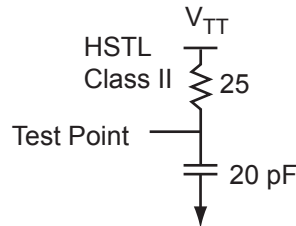


Figure 2-18 • AC Loading

Table 2-94 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	VREF (typ.) (V)	VTT (typ.) (V)	C _{LOAD} (pF)
VREF - 0.1	VREF + 0.1	0.75	0.75	0.75	20

Note: *Measuring point = V_{trip}. See Table 2-23 on page 2-23 for a complete table of trip points.

Timing Characteristics

1.5 V DC Core Voltage

Table 2-95 • HSTL Class II – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V,
Worst-Case VCCI = 1.4 V VREF = 0.75 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
Std.	0.98	2.62	0.19	1.77	0.67	2.66	2.40			6.29	6.03	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

1.2 V DC Core Voltage

Table 2-96 • HSTL Class II – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V,
Worst-Case VCCI = 1.4 V VREF = 0.75 V

Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{ZL}	t _{ZH}	t _{LZ}	t _{HZ}	t _{ZLS}	t _{ZHS}	Units
Std.	1.55	2.93	0.26	1.94	1.10	2.98	2.75			8.79	8.55	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

I/O Register Specifications

Fully Registered I/O Buffers with Synchronous Enable and Asynchronous Preset

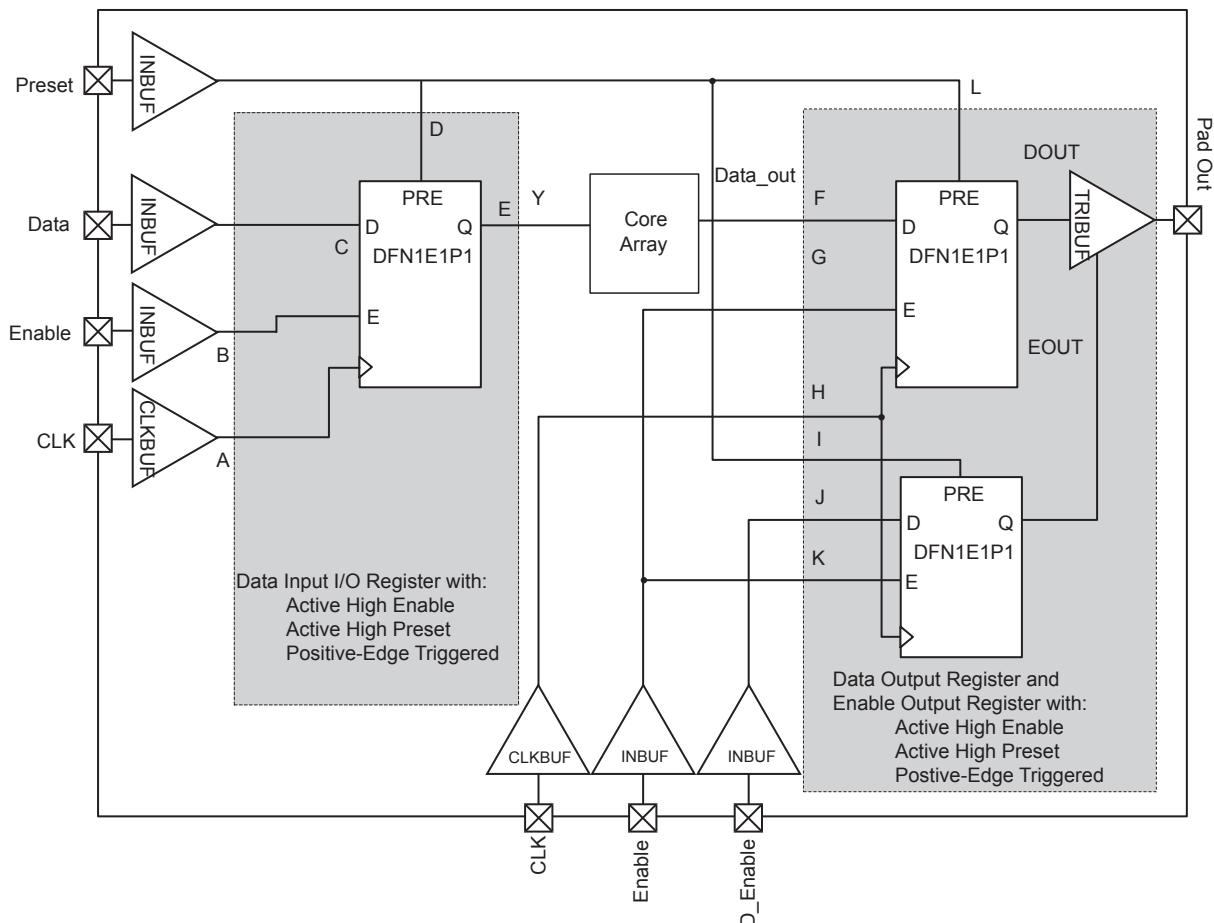
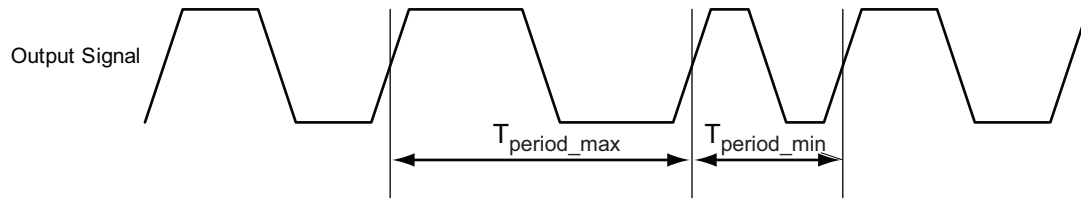


Figure 2-26 • Timing Model of Registered I/O Buffers with Synchronous Enable and Asynchronous Preset



Note: Peak-to-peak jitter measurements are defined by $T_{\text{peak-to-peak}} = T_{\text{period_max}} - T_{\text{period_min}}$.

Figure 2-40 • Peak-to-Peak Jitter Definition

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-145 • RAM4K9

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{AS}	Address Setup Time	0.83	ns
t_{AH}	Address Hold Time	0.16	ns
t_{ENS}	REN, WEN Setup Time	0.81	ns
t_{ENH}	REN, WEN Hold Time	0.16	ns
t_{BKS}	BLK Setup Time	1.65	ns
t_{BKH}	BLK Hold Time	0.16	ns
t_{DS}	Input Data (DIN) Setup Time	0.71	ns
t_{DH}	Input Data (DIN) Hold Time	0.36	ns
t_{CKQ1}	Clock HIGH to New Data Valid on DOUT (output retained, WMODE = 0)	3.53	ns
	Clock HIGH to New Data Valid on DOUT (flow-through, WMODE = 1)	3.06	ns
t_{CKQ2}	Clock HIGH to New Data Valid on DOUT (pipelined)	1.81	ns
t_{C2CWWL}^1	Address collision clk-to-clk delay for reliable write after write on same address; applicable to closing edge	0.23	ns
t_{C2CRWH}^1	Address collision clk-to-clk delay for reliable read access after write on same address; applicable to opening edge	0.35	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address; applicable to opening edge	0.41	ns
t_{RSTBQ}	RESET Low to Data Out Low on DOUT (flow-through)	2.06	ns
	RESET Low to Data Out Low on DOUT (pipelined)	2.06	ns
$t_{REMRSTB}$	RESET Removal	0.61	ns
$t_{RECRSTB}$	RESET Recovery	3.21	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.68	ns
t_{CYC}	Clock Cycle Time	6.24	ns
F_{MAX}	Maximum Frequency	160	MHz

Notes:

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 3-1 shows the Flash*Freeze pin location on the available packages. The Flash*Freeze pin location is independent of device (except for a PQ208 package), allowing migration to larger or smaller IGLOO devices while maintaining the same pin location on the board. Refer to the "Flash*Freeze Technology and Low Power Modes" chapter of the *IGLOOe FPGA Fabric User's Guide* for more information on I/O states during Flash*Freeze mode.

Table 3-1 • Flash*Freeze Pin Locations for IGLOOe Devices

Package	Flash*Freeze Pin
FG256	T3
FG484	W6
FG896	AH4

JTAG Pins

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the part must be supplied to allow JTAG signals to transition the device. Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

TCK

Test Clock

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pull-up/-down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500 Ω to 1 k Ω will satisfy the requirements. Refer to Table 3-2 for more information.

Table 3-2 • Recommended Tie-Off Values for the TCK and TRST Pins

VJTAG	Tie-Off Resistance ^{1,2}
VJTAG at 3.3 V	200 Ω to 1 k Ω
VJTAG at 2.5 V	200 Ω to 1 k Ω
VJTAG at 1.8 V	500 Ω to 1 k Ω
VJTAG at 1.5 V	500 Ω to 1 k Ω

Notes:

1. The TCK pin can be pulled-up or pulled-down.
2. The TRST pin is pulled-down.
3. Equivalent parallel resistance if more than one device is on the JTAG chain

Related Documents

User's Guides

IGLOOe FPGA Fabric User's Guide

http://www.microsemi.com/soc/documents/IGLOOe_UG.pdf

Packaging Documents

The following documents provide packaging information and device selection for low power flash devices.

Product Catalog

http://www.microsemi.com/soc/documents/ProdCat_PIB.pdf

Lists devices currently recommended for new designs and the packages available for each member of the family. Use this document or the datasheet tables to determine the best package for your design, and which package drawing to use.

Package Mechanical Drawings

<http://www.microsemi.com/soc/documents/PckgMechDrwns.pdf>

This document contains the package mechanical drawings for all packages currently or previously supplied by Microsemi. Use the bookmarks to navigate to the package mechanical drawings.

Additional packaging materials: <http://www.microsemi.com/soc/products/solutions/package/docs.aspx>.

FG896	
Pin Number	AGLE3000 Function
AK14	IO197PDB5V0
AK15	IO191NDB4V4
AK16	IO191PDB4V4
AK17	IO189NDB4V4
AK18	IO189PDB4V4
AK19	IO179PPB4V3
AK20	IO175NDB4V2
AK21	IO175PDB4V2
AK22	IO169NDB4V1
AK23	IO169PDB4V1
AK24	GND
AK25	IO167PPB4V1
AK26	GND
AK27	GDC2/IO156PPB4V0
AK28	GND
AK29	GND
B1	GND
B2	GND
B3	GAA2/IO309PPB7V4
B4	VCC
B5	IO14PPB0V1
B6	VCC
B7	IO07PPB0V0
B8	IO09PDB0V1
B9	IO15PPB0V1
B10	IO19NDB0V2
B11	IO19PDB0V2
B12	IO29NDB0V3
B13	IO29PDB0V3
B14	IO31PPB0V3
B15	IO37NDB0V4
B16	IO37PDB0V4
B17	IO41PDB1V0
B18	IO51NDB1V1
B19	IO59PDB1V2

FG896	
Pin Number	AGLE3000 Function
B20	IO53PDB1V1
B21	IO53NDB1V1
B22	IO61NDB1V2
B23	IO61PDB1V2
B24	IO69NPB1V3
B25	VCC
B26	GBC0/IO79NPB1V4
B27	VCC
B28	IO64NPB1V2
B29	GND
B30	GND
C1	GND
C2	IO309NPB7V4
C3	VCC
C4	GAA0/IO00NPB0V0
C5	VCCIB0
C6	IO03PDB0V0
C7	IO03NDB0V0
C8	GAB1/IO01PDB0V0
C9	IO05PDB0V0
C10	IO15NPB0V1
C11	IO25NDB0V3
C12	IO25PDB0V3
C13	IO31NPB0V3
C14	IO27NDB0V3
C15	IO39NDB0V4
C16	IO39PDB0V4
C17	IO55PPB1V1
C18	IO51PDB1V1
C19	IO59NDB1V2
C20	IO63NDB1V2
C21	IO63PDB1V2
C22	IO67NDB1V3
C23	IO67PDB1V3
C24	IO75NDB1V4

FG896	
Pin Number	AGLE3000 Function
C25	IO75PDB1V4
C26	VCCIB1
C27	IO64PPB1V2
C28	VCC
C29	GBA1/IO81PPB1V4
C30	GND
D1	IO303PPB7V3
D2	VCC
D3	IO305NPB7V3
D4	GND
D5	GAA1/IO00PPB0V0
D6	GAC1/IO02PDB0V0
D7	IO06NPB0V0
D8	GAB0/IO01NDB0V0
D9	IO05NDB0V0
D10	IO11NDB0V1
D11	IO11PDB0V1
D12	IO23NDB0V2
D13	IO23PDB0V2
D14	IO27PDB0V3
D15	IO40PDB0V4
D16	IO47NDB1V0
D17	IO47PDB1V0
D18	IO55NPB1V1
D19	IO65NDB1V3
D20	IO65PDB1V3
D21	IO71NDB1V3
D22	IO71PDB1V3
D23	IO73NDB1V4
D24	IO73PDB1V4
D25	IO74NDB1V4
D26	GBB0/IO80NPB1V4
D27	GND
D28	GBA0/IO81NPB1V4
D29	VCC

FG896	
Pin Number	AGLE3000 Function
V26	IO126NDB3V1
V27	IO129NDB3V1
V28	IO127NDB3V1
V29	IO125NDB3V1
V30	IO123PDB3V1
W1	IO266NDB6V4
W2	IO262NDB6V3
W3	IO260NDB6V3
W4	IO252NDB6V2
W5	IO251NDB6V2
W6	IO251PDB6V2
W7	IO255NDB6V2
W8	IO249PPB6V1
W9	IO253PDB6V2
W10	VCCIB6
W11	VCC
W12	GND
W13	GND
W14	GND
W15	GND
W16	GND
W17	GND
W18	GND
W19	GND
W20	VCC
W21	VCCIB3
W22	IO134PDB3V2
W23	IO138PDB3V3
W24	IO132NDB3V2
W25	IO136NPB3V2
W26	IO130NPB3V2
W27	IO141PDB3V3
W28	IO135PDB3V2
W29	IO131PDB3V2
W30	IO123NDB3V1

FG896	
Pin Number	AGLE3000 Function
Y1	IO266PDB6V4
Y2	IO250PDB6V2
Y3	IO250NDB6V2
Y4	IO246PDB6V1
Y5	IO247NDB6V1
Y6	IO247PDB6V1
Y7	IO249NPB6V1
Y8	IO245PDB6V1
Y9	IO253NDB6V2
Y10	GEB0/IO235NPB6V0
Y11	VCC
Y12	VCC
Y13	VCC
Y14	VCC
Y15	VCC
Y16	VCC
Y17	VCC
Y18	VCC
Y19	VCC
Y20	VCC
Y21	IO142PPB3V3
Y22	IO134NDB3V2
Y23	IO138NDB3V3
Y24	IO140NDB3V3
Y25	IO140PDB3V3
Y26	IO136PPB3V2
Y27	IO141NDB3V3
Y28	IO135NDB3V2
Y29	IO131NDB3V2
Y30	IO133PDB3V2

Revision	Changes	Page
Advance v0.4 (December 2007)	The Table 1 • IGLOOe Product Family table was updated to change the maximum number of user I/Os for AGLE3000.	I
	The "IGLOOe FPGAs Package Sizes Dimensions" table is new. Package dimensions were removed from the "I/Os Per Package¹" table. The number of I/Os was updated for FG896.	II
	A note regarding marking information was added to the "IGLOOe Ordering Information" table.	III
	Table 2-4 • IGLOOe CCC/PLL Specification and Table 2-5 • IGLOOe CCC/PLL Specification were updated.	2-18, 2-19
	The "During Flash*Freeze Mode" section was updated to include information about the output of the I/O to the FPGA core.	2-60
	Figure 2-38 • Flash*Freeze Mode Type 1 – Timing Diagram was updated to modify the LSICC signal.	2-56
	Table 2-32 • Flash*Freeze Pin Location in IGLOOe Family Packages (device-independent) was updated for the FG896 package.	2-64
	Figure 2-40 • Flash*Freeze Mode Type 2 – Timing Diagram was updated to modify the LSICC Signal.	2-58
	Information regarding calculation of the quiescent supply current was added to the "Quiescent Supply Current" section.	3-6
	Table 3-8 • Quiescent Supply Current (IDD), IGLOOe Flash*Freeze Mode† was updated.	3-6
	Table 3-9 • Quiescent Supply Current (IDD), IGLOOe Sleep Mode (VCC = 0 V)† was updated.	3-6
	Table 3-11 • Quiescent Supply Current, No IGLOOe Flash*Freeze Mode ¹ was updated.	3-6
	Table 3-99 • Minimum and Maximum DC Input and Output Levels was updated.	3-51
	Table 3-136 • JTAG 1532 and Table 3-135 • JTAG 1532 were updated.	3-95
	The "484-Pin FBGA" table for AGLE3000 is new.	4-11
	The "896-Pin FBGA" package and table for AGLE3000 is new.	4-16
Advance v0.3 (September 2007)	Cortex-M1 device information was added to the Table 1 • IGLOOe Product Family table, the "I/Os Per Package 1" table, "IGLOOe Ordering Information" , and "Temperature Grade Offerings" .	I, II, III, IV
Advance v0.2	The words "ambient temperature" were added to the temperature range in the "IGLOOe Ordering Information" , "Temperature Grade Offerings" , and "Speed Grade and Temperature Grade Matrix" sections.	III, IV
	The T _J parameter in Table 3-2 • Recommended Operating Conditions was changed to T _A , ambient temperature, and table notes 6–8 were added.	3-2

